

2SD1265, 2SD1265A

Silicon NPN Triple-Diffused Junction Type

Power Amplifier

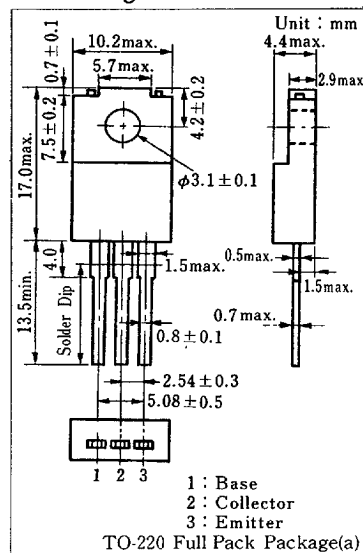
■ Features

- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings (Tc=25°C)

Item		Symbol	Value	Unit
Collector-base voltage	2SD1265	V_{CBO}	60	V
	2SD1265A		80	
Collector-emitter voltage	2SD1265	V_{CEO}	60	V
	2SD1265A		80	
Emitter-base voltage		V_{EBO}	8	V
Peak collector current		I_{CP}	6	A
Collector current		I_C	4	A
Base-emitter voltage		I_B	1	A
Collector power dissipation	T _c = 25 °C	P _c	30	W
	T _a = 25 °C		2	
Junction temperature		T _j	150	°C
Storage temperature		T _{stg}	-55 ~ +150	°C

■ Package Dimensions



■ Electrical Characteristics (Tc=25°C)

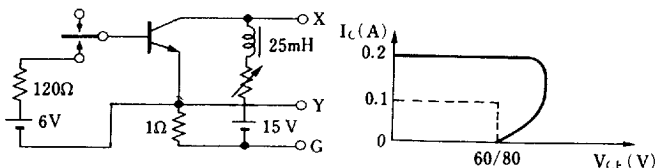
Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB}=20\text{ V}, I_E=0$			30	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=8\text{ V}, I_C=0$			1	mA
Collector-emitter voltage	2SD1265	$V_{CEO(sus)}^{*2}$ $I_C=0.2\text{ A}, L=25\text{ mH}$	60			V
	2SD1265A		80			
DC current gain	h_{FE1}	$V_{CE}=3\text{ V}, I_C=0.1\text{ A}$	40			
	h_{FE2}^{*1}	$V_{CE}=3\text{ V}, I_C=1\text{ A}$	30		160	
Base-emitter voltage	V_{BE}	$V_{CE}=3\text{ V}, I_C=1\text{ A}$			1.2	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{ A}, I_B=0.4\text{ A}$			1	V
Transition frequency	f_T	$V_{CE}=10\text{ V}, I_C=0.2\text{ A}, f=0.5\text{ MHz}$		1		MHz

*1 h_{FE2} Classifications

Class	Q	P	O
h_{FE2}	30 ~ 60	50 ~ 100	80 ~ 160

*2 $V_{CEO(sus)}$ Test method

Mercury relay 50/60 Hz

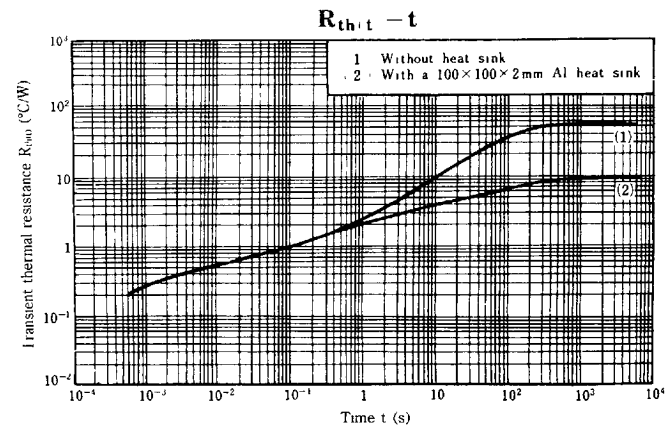
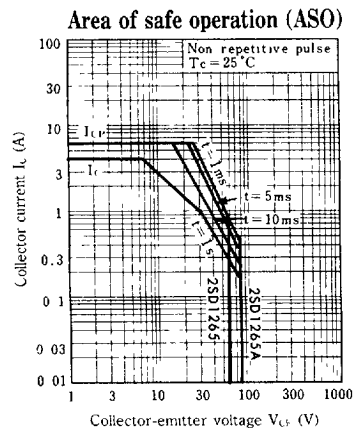
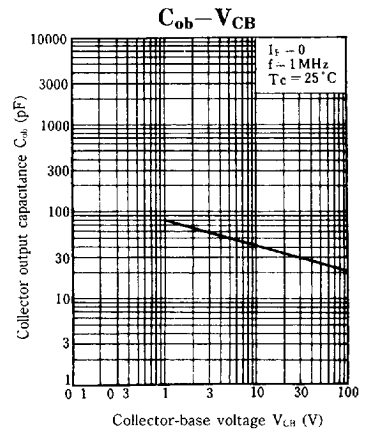
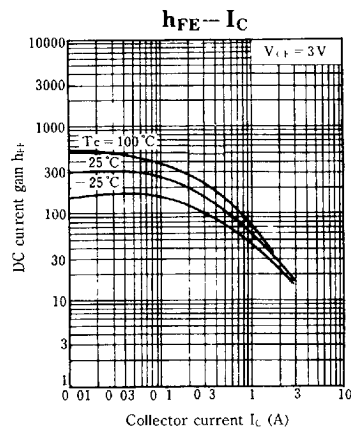
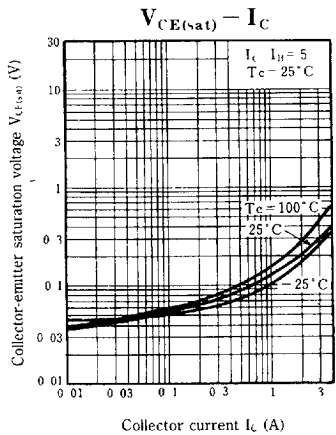
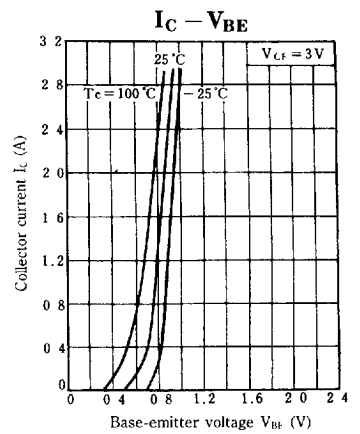
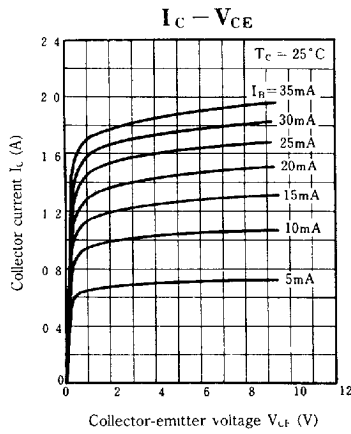
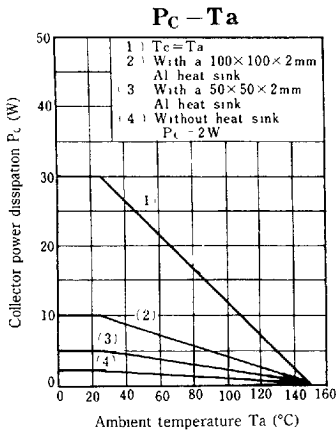


2SD1265/2SD1265A

Panasonic

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